

40V N-Channel Power SpeedFET

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load Switch

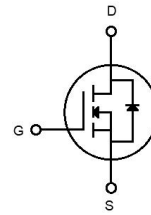
• Ordering Information:

Part NO.	ZMS005N04HB6
Marking	ZMS005N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	800

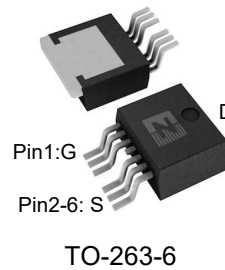
• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage ^①	V_{GS}		±20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	300	A
	I_D	$T_C=75^\circ\text{C}$	300	A
	I_D	$T_C=100^\circ\text{C}$	275	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	1200	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	278	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.5	W
Operating Junction Temperature	T_J		-55 to +150	°C
Storage Temperature	T_{STG}		-55 to +150	°C
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	756	mJ
		L=0.5mH, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	1210	mJ
ESD Level (HBM)	CLASS 2			

• Product Summary



$V_{DS} = 40\text{V}$
 $R_{DS(ON)} = 0.55\text{m}\Omega$
 $I_D = 300\text{A}$



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.45	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{②}$		-	36	°C/W
Soldering temperature	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2	2.7	4	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$		0.55	0.7	m Ω
Forward Transconductance	g_{FS}	$V_{GS}=5V, I_{SD}=10A$		30		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=40A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	10620	-	pF
Output capacitance	C_{oss}		-	2810	-	
Reverse transfer capacitance	C_{rss}		-	115	-	
Gate Resistance	R_g	$f=1MHz$	-	1.6		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	155	-	nC
Gate - Source charge	Q_{gs}		-	35	-	
Gate - Drain charge	Q_{gd}		-	32	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	65	-	ns
Turn-ON Rise time	t_r		-	31	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	85	-	ns
Turn-Off Fall time	t_f		-	78	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, di_S/dt=100A/\mu s, I_S=50A$	-	97	-	ns
Reverse Recovery Charge	Q_{RR}		-	135	-	nC

Fig.1 Gate-Charge Characteristics

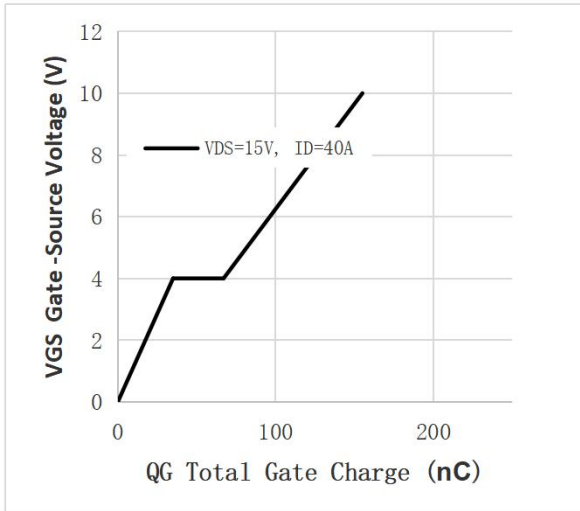


Fig.2 Capacitance Characteristics

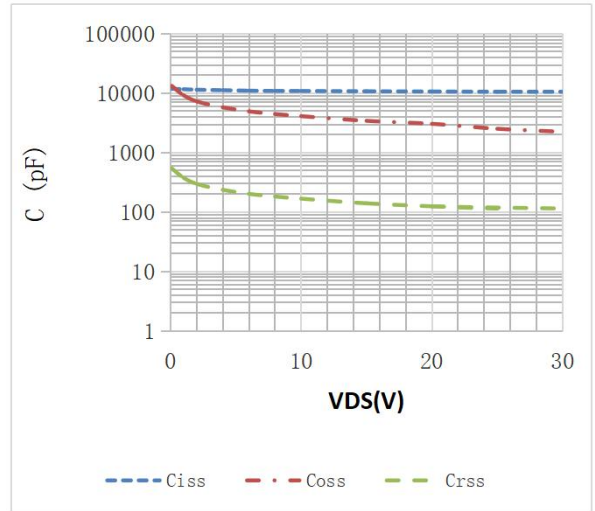


Fig.3 Power Dissipation

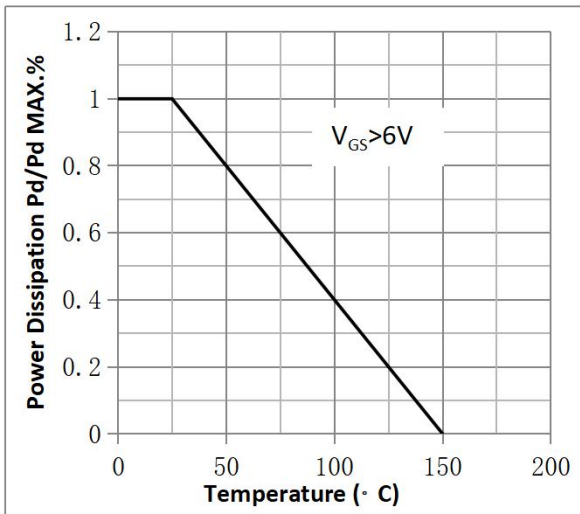


Fig.4 Typical output Characteristics

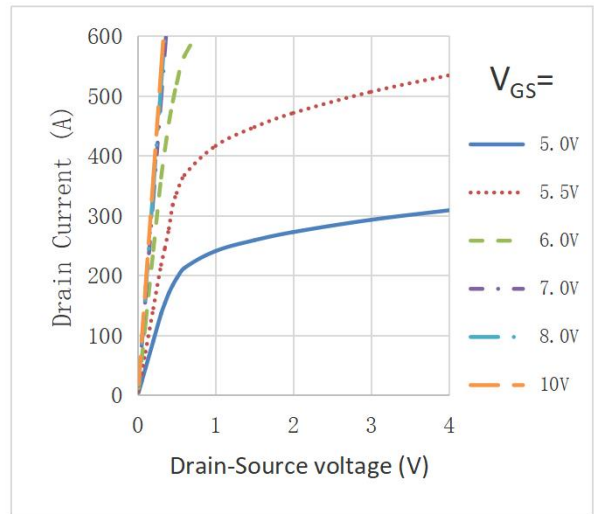


Fig.5 Threshold Voltage V.S Junction Temperature

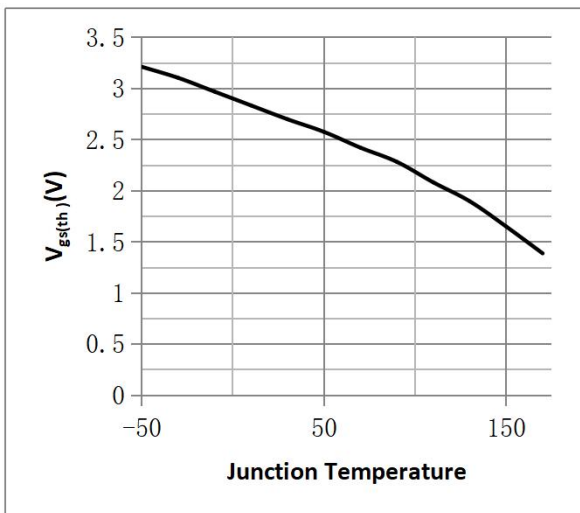


Fig.6 Resistance V.S Drain Current

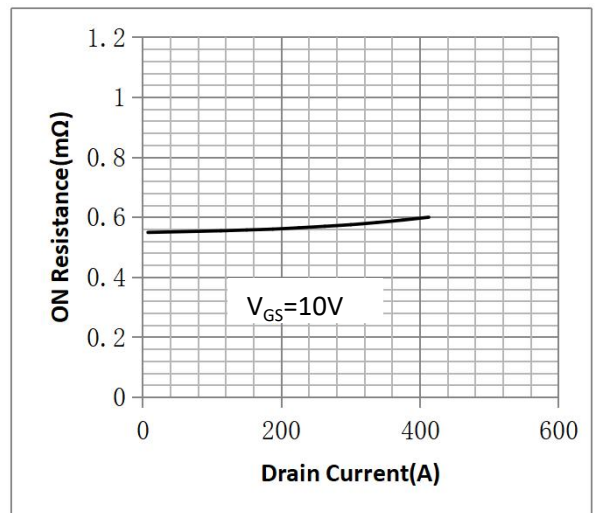


Fig.7 On-Resistance VS Gate Source Voltage

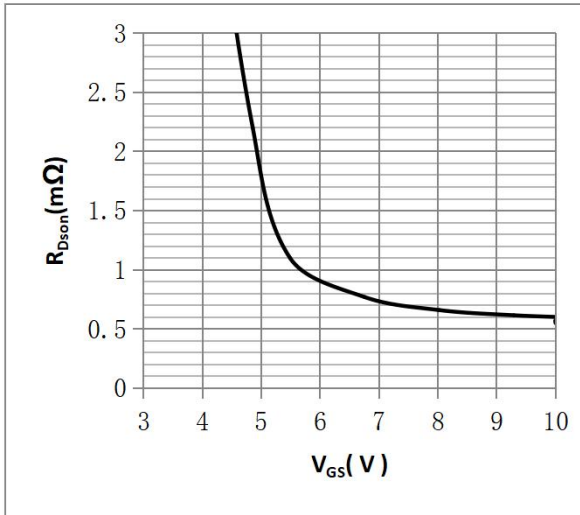


Fig.8 On-Resistance V.S Junction Temperature

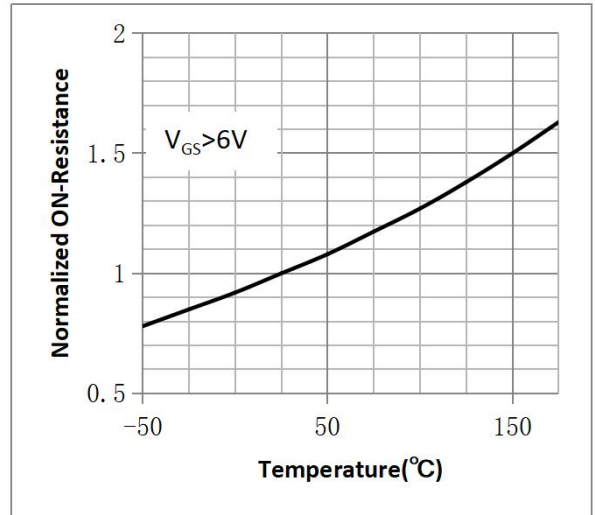


Figure 9. Diode Forward Voltage vs. Current

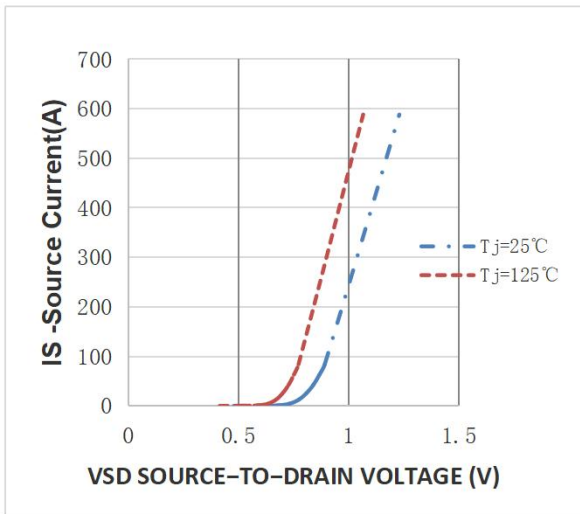


Figure 10. Transfer Characteristics

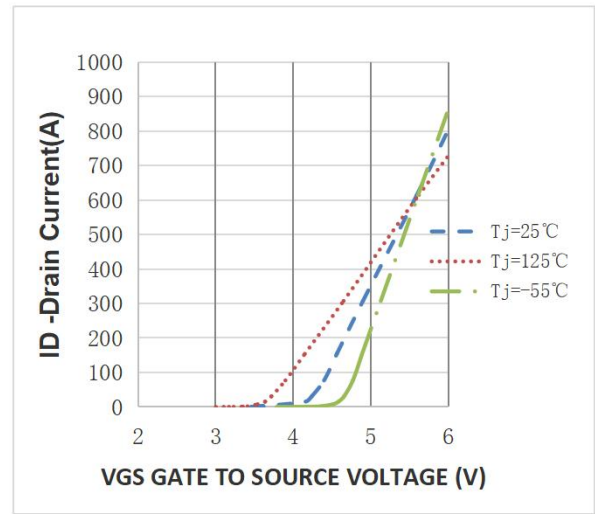


Fig.11 Safe Operating Area

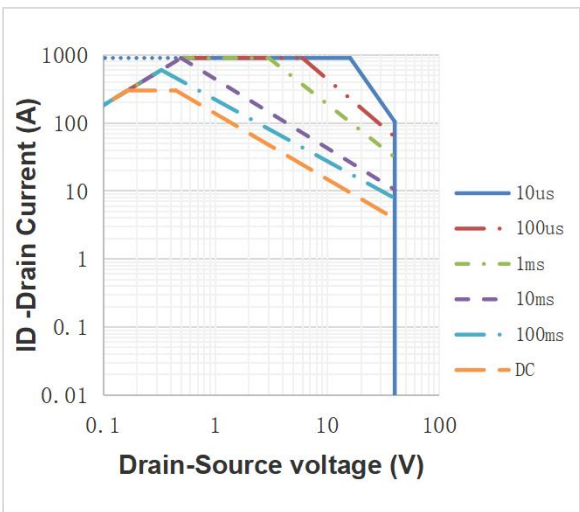
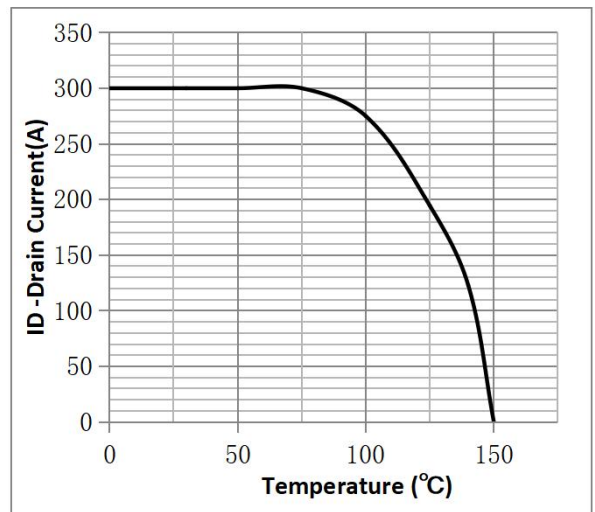
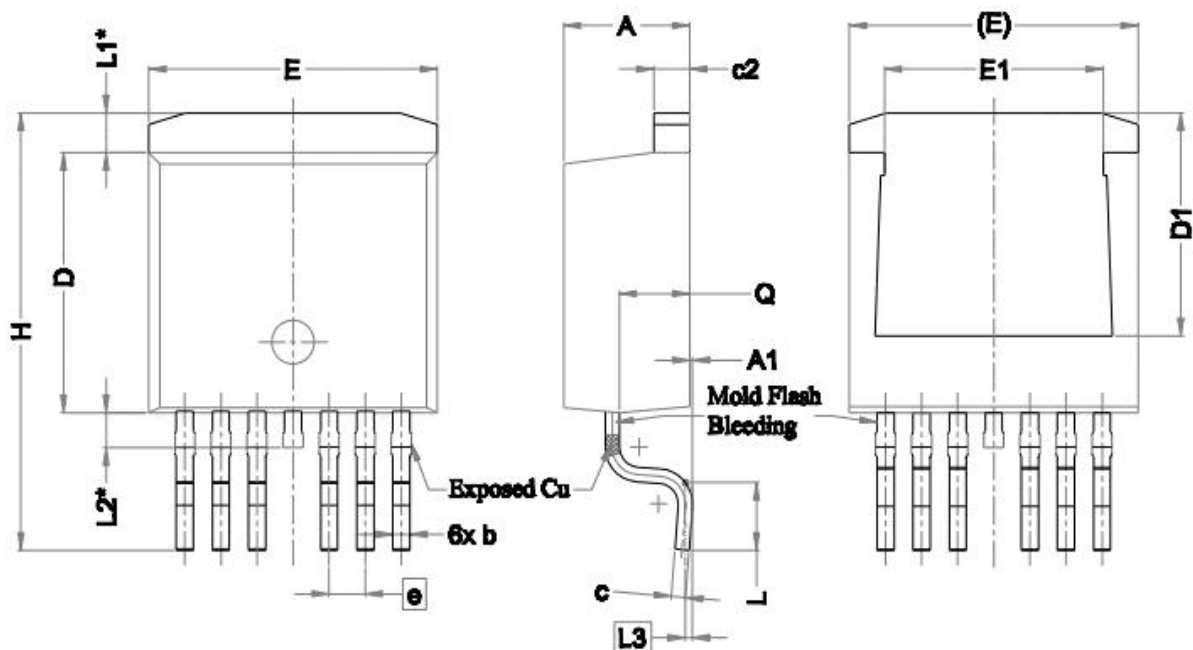


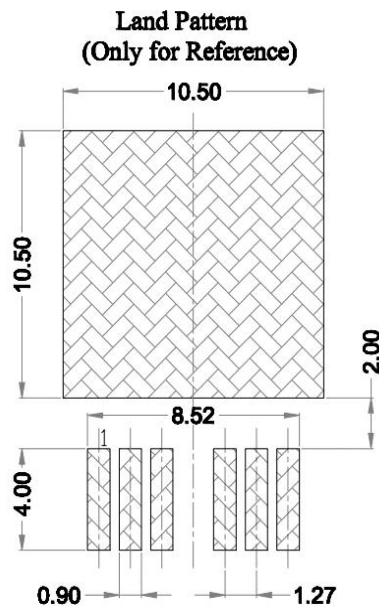
Fig.12 ID vs. Junction Temperature^③



•TO-263-6 Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.20 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70



Note:

① Pulse : VGS=+20V/-20V, Duty cycle=50%, Tj=175°C, t=1000 hours; For DC , the following test conditions can be passed: VGS=+20V/-10V, Tj=175°C, t=1000 hours;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

③ Practically the current will be limited by PCB, thermal design and operating temperature.
VGS=10V.

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Revision History

Version	Date	Change
A	2023.1.15	new
B	2023.5.10	1.Add Reach, HF figure 2.ID curve modify